

















-  Drafts
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 -  L1: (0)
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☒ Highlight all hit terms initially

3	and AlSGaSN	and AlSGaInSN
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 **BRS**  **IS&R**  **Image**  **Text**  **HTML**

	U	1	Document ID	Issue Dat	Pages	Title	Current OR	Current XI
1	✓	✓	US 6579780	20030617	40	Method for growing a compound semiconductor.	438/479	438/46; 438/483
2	✓	✓	US 6542526	20030401	39	Optical information processor and semicondu	372/45	372/46
3	✓	✓	US 6537838	20030325	7	Forming semiconductor structures including ac	438/22	257/96; 438/46
4	✓	✓	US 6530991	20030311	28	Method for the formation of semiconduc	117/89	117/103; 117/106;
5	✓	✓	US 6526083	20030225	15	Two section blue laser diode with reduced outp	372/50	438/48
6	✓	✓	US 6508879	20030121	9	Method of fabricating group III-V nitride com	117/104	117/101; 117/952
7	✓	✓	US 6455340	20020924	8	Method of fabricating GaN semiconductor struc	438/31	438/39; 438/47
8	✓	✓	US 6379985	20020430	21	Methods for cleaving facets in III-V nitride	438/33	257/E29.00 4;
9	✓	✓	US 6345063	20020205	14	Algainn elog led and laser diode structures	372/45	257/14; 257/E33.02
10	✓	✓	US 6342405	20020129	21	Methods for forming group III-arsenide-nitr	438/46	257/E33.02 8
11	✓	✓	US 6285696	20010904	16	Algainn pendeoeptaxy led and laser diode str	438/22	257/14; 257/E33.02

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